

UT54ACS4002/UT54ACTS4002

**Radiation-Hardened
Dual 4-Input NOR Gates**

FEATURES

- 1.2μ radiation-hardened CMOS
 - Latchup immune
- High speed
- Low power consumption
- Single 5 volt supply
- Available QML Q or V processes
- Flexible package
 - 14-pin DIP
 - 14-lead flatpack

DESCRIPTION

The UT54ACS4002 and the UT54ACTS4002 are dual 4-input NOR gates. A high on any input forces the output to a low state. The circuits perform the Boolean functions:

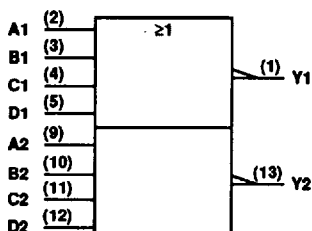
$$Y = A + B + C + D = \overline{A \cdot B \cdot C \cdot D}$$

The devices are characterized over full military temperature range of -55°C to +125°C.

FUNCTION TABLE

INPUTS				OUTPUT
A _n	B _n	C _n	D _n	Y _n
L	L	L	L	H
H	X	X	X	L
X	H	X	X	L
X	X	H	X	L
X	X	X	H	L

LOGIC SYMBOL

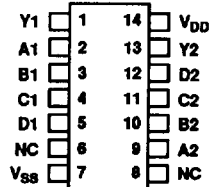


Note:

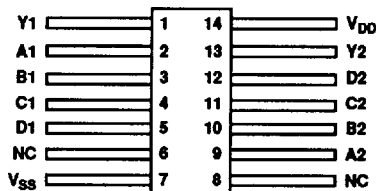
1. Logic symbol in accordance with ANSI/IEEE standard 91-1984 and IEC Publication 617-12.

PINOUTS

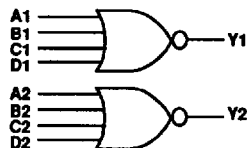
**14-Pin DIP
Top View**



**14-Lead Flatpack
Top View**



LOGIC DIAGRAM



RADIATION HARDNESS SPECIFICATIONS ¹

PARAMETER	LIMIT	UNITS
Total Dose	1.0E6	rads(Si)
SEU & SEL Threshold ²	80	MeV-cm ² /mg
Neutron Fluence	1.0E14	n/cm ²

Notes:

1. Logic will not latchup during radiation exposure within the limits defined in the table.

2. Device storage elements are immune to SEU affects.

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	LIMIT	UNITS
V _{DD}	Supply voltage	-0.3 to 7.0	V
V _{IO}	Voltage any pin	-.3 to V _{DD} +.3	V
T _{STG}	Storage Temperature range	-65 to +150	°C
T _J	Maximum junction temperature	+175	°C
T _{LS}	Lead temperature (soldering 5 seconds)	+300	°C
Θ _{JC}	Thermal resistance junction to case	20	°C/W
I _I	DC input current	±10	mA
P _D	Maximum power dissipation	1	W

Note:

1. Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, functional operation of the device at these or any other conditions beyond limits indicated in the operational sections is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMIT	UNITS
V _{DD}	Supply voltage	4.5 to 5.5	V
V _{IN}	Input voltage any pin	0 to V _{DD}	V
T _C	Temperature range	-55 to + 125	°C

DC ELECTRICAL CHARACTERISTICS ⁷(V_{DD} = 5.0V ±10%; V_{SS} = 0V ⁶, -55°C < T_C < +125°C)

SYMBOL	PARAMETER	CONDITION	MIN	MAX	UNIT
V _{IL}	Low-level input voltage ¹ ACTS ACS			0.8 .3V _{DD}	V
V _{IH}	High-level input voltage ¹ ACTS ACS		.5V _{DD} .7V _{DD}		V
I _{IN}	Input leakage current ACTS/ACS	V _{IN} = V _{DD} or V _{SS}	-1	1	μA
V _{OL}	Low-level output voltage ³ ACTS ACS	I _{OL} = 8.0mA I _{OL} = 100μA		0.40 0.25	V
V _{OH}	High-level output voltage ³ ACTS ACS	I _{OH} = -8.0mA I _{OH} = -100μA	.7V _{DD} V _{DD} - 0.25		V
I _{OS}	Short-circuit output current ^{2,4} ACTS/ACS	V _O = V _{DD} and V _{SS}	-200	200	mA
P _{total}	Power dissipation ^{8,9}	C _L = 50pF		1.9	mW/ MHz
I _{DDQ}	Quiescent Supply Current	V _{DD} = 5.5V		10	μA
C _{IN}	Input capacitance ⁵	f = 1MHz @ 0V		15	pF
C _{OUT}	Output capacitance ⁵	f = 1MHz @ 0V		15	pF

Notes:

- Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions: V_{IH} = V_{IH}(min) + 20%, - 0%; V_{IL} = V_{IL}(max) + 0%, - 50%, as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to V_{IH}(min) and V_{IL}(max).
- Supplied as a design limit but not guaranteed or tested.
- Per MIL-M-38510, for current density ≤ 5.0E5 amps/cm², the maximum product of load capacitance (per output buffer) times frequency should not exceed 3,765 pF MHz.
- Not more than one output may be shorted at a time for maximum duration of one second.
- Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and V_{SS} at frequency of 1MHz and a signal amplitude of 50mV rms maximum.
- Maximum allowable relative shift equals 50mV.
- All specifications valid for radiation dose ≤ 1E6 rads(Si).
- Power does not include power contribution of any TTL output sink current.
- Power dissipation specified per switching output.

AC ELECTRICAL CHARACTERISTICS ²(V_{DD} = 5.0V ±10%; V_{SS} = 0V ¹, -55°C < T_C < +125°C)

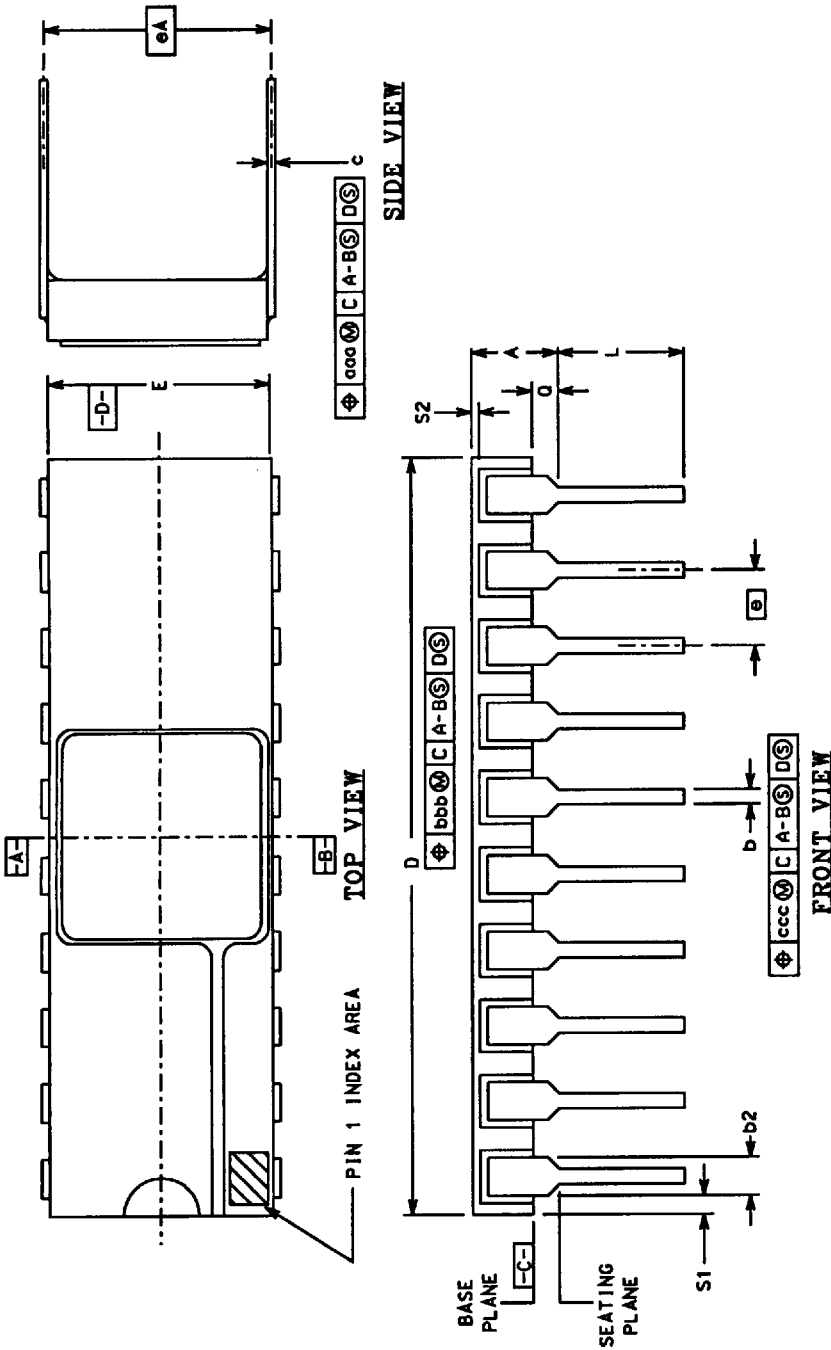
SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNIT
t _{PHL}	Input to output	1	12	ns
t _{PLH}	Input to output	2	14	ns

Notes:

- Maximum allowable relative shift equals 50mV.
- All specifications valid for radiation dose ≤ 1E6 rads(Si).

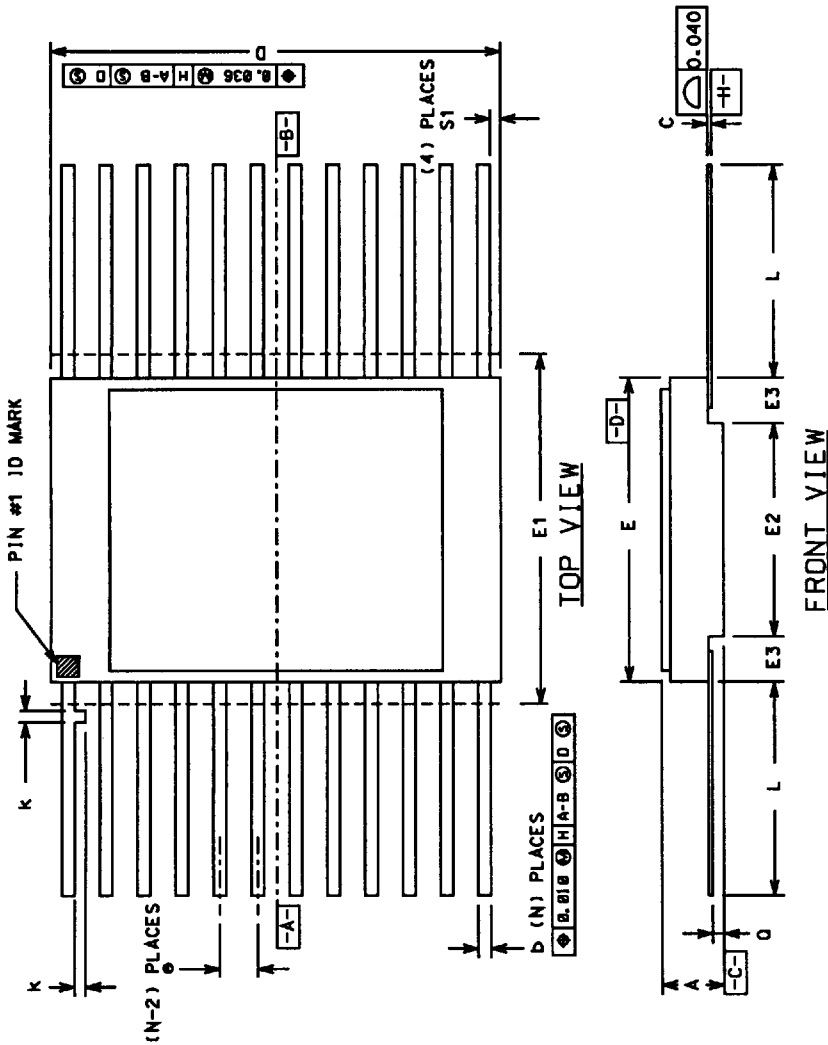
2.0 RAD-HARD MSI PACKAGES

Side-Brazed Packages



MIL-STD-1835 DWG		DIMENSION SYMBOLS														Dwg	
		A	B	C	D	E	F	G	H	I	J	K	L	M	N	O	P
PKG	LEAD	0.200	0.026	0.065	0.018	0.310	0.100	0.300	0.060	0.015	0.005	0.005	0.200	0.125	0.300	0.060	0.010
CONF	IG	0.200	0.014	0.045	0.008	0.220	0.080	0.220	0.015	0.015	0.005	0.005	0.200	0.125	0.300	0.060	0.010
14	D-1	0.200	0.026	0.065	0.018	0.310	0.100	0.300	0.060	0.015	0.005	0.005	0.200	0.125	0.300	0.060	0.010
16	D-2	0.200	0.014	0.045	0.008	0.220	0.080	0.220	0.015	0.015	0.005	0.005	0.200	0.125	0.300	0.060	0.010
20	D-8	0.200	0.026	0.065	0.018	0.310	0.100	0.300	0.060	0.015	0.005	0.005	0.200	0.125	0.300	0.060	0.010
		0.014	0.014	0.045	0.008	0.220	0.080	0.220	0.015	0.015	0.005	0.005	0.200	0.125	0.300	0.060	0.010

Flatpack Packages



PKG CONF IG	LEAD COUNT	MIL-STD 1836 DWG CONF B	DIMENSION SYMBOLS												
			A	b	c	D	E	E1	E2	E3	e	k	L	O	S1
-03	14	F-2A	0.115	0.022	0.009	0.390	0.260	0.290	---	---	---	0.050	0.370	0.045	---
			0.045	0.015	0.004	0.235	0.235	0.130	0.030	BSC	0.008	0.270	0.026	0.005	
-04	16	F-5A	0.115	0.022	0.009	0.440	0.285	0.315	---	---	---	0.050	0.370	0.045	---
			0.045	0.015	0.004	0.245	0.245	0.130	0.030	BSC	0.008	0.250	0.026	0.005	
-05	20	F-9A	0.115	0.022	0.009	0.540	0.300	0.330	---	---	---	0.050	0.370	0.045	---
			0.045	0.015	0.004	0.245	0.245	0.130	0.030	BSC	0.008	0.250	0.026	0.000	